

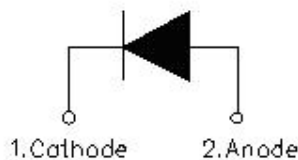
SDUR60Q60W ULTRAFAST RECTIFIER



Applications:

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Circuit Diagram



Features:

- Ultra-Fast switching
- High current capability
- Low reverse leakage current
- High surge current capability
- Plastic Material has UL Flammability Classification 94V-O
- Terminals finish: 100% Pure Tin
- This is a Pb – free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	600	V
Average Rectified Forward Current	$I_F(AV)$	50% duty cycle @ $T_c=70^\circ\text{C}$, rectangular wave form	60	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3ms, Half Sine pulse	400	A

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-	-55 to +175	$^\circ\text{C}$
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	0.34	$^\circ\text{C/W}$
Approximate Weight	wt	-	6.28	g
Case Style	TO-247AC			

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 30A, Pulse, $T_J = 25^{\circ}\text{C}$	1.9	-	V
		@ 60A, Pulse, $T_J = 25^{\circ}\text{C}$	2.3	2.4	V
	V_{F2}	@ 30A, Pulse, $T_J = 125^{\circ}\text{C}$	1.6	-	V
	V_{F3}	@ 30A, Pulse, $T_J = 150^{\circ}\text{C}$	1.5	-	V
Reverse Current*	I_{R1}	@ $V_R = \text{rated } V_R$, $T_J = 25^{\circ}\text{C}$	0.08	25	μA
	I_{R2}	@ $V_R = \text{rated } V_R$, $T_J = 125^{\circ}\text{C}$	197	500	μA
	I_{R3}	@ $V_R = \text{rated } V_R$, $T_J = 150^{\circ}\text{C}$	850	-	μA
Reverse Recovery Time	t_{rr1}	$I_F = 500\text{mA}$, $I_R = 1\text{A}$, and $I_{rm} = 250\text{mA}$, $T_J = 25^{\circ}\text{C}$	36	40	ns
Reverse Recovery Time	t_{rr}	$I_F = 60\text{A}$, $di_F/dt = -1000\text{A}/\mu\text{s}$ $V_R = 400\text{V}$, $T_J = 25^{\circ}\text{C}$	44	-	ns
Reverse Recovery Charge	Q_{rr}		194	-	nC
Reverse Recovery Current	I_{RRM}		8.8	-	A
Reverse Recovery Time	t_{rr}	$I_F = 60\text{A}$, $di_F/dt = -1000\text{A}/\mu\text{s}$ $V_R = 400\text{V}$, $T_J = 125^{\circ}\text{C}$	169	-	ns
Reverse Recovery Charge	Q_{rr}		1217	-	nC
Reverse Recovery Current	I_{RRM}		14.4	-	A
Reverse Recovery Time	t_{rr}	$I_F = 30\text{A}$, $di_F/dt = -200\text{A}/\mu\text{s}$ $V_R = 400\text{V}$, $T_J = 25^{\circ}\text{C}$	86	-	ns
Reverse Recovery Charge	Q_{rr}		206	-	nC
Reverse Recovery Current	I_{RRM}		4.8	-	A
Reverse Recovery Time	t_{rr}	$I_F = 30\text{A}$, $di_F/dt = -200\text{A}/\mu\text{s}$ $V_R = 400\text{V}$, $T_J = 125^{\circ}\text{C}$	148	-	ns
Reverse Recovery Charge	Q_{rr}		562	-	nC
Reverse Recovery Current	I_{RRM}		7.6	-	A
Reverse Recovery Time	t_{rr}	$I_F = 1\text{A}$, $di_F/dt = -100\text{A}/\mu\text{s}$ $V_R = 30\text{V}$, $T_J = 25^{\circ}\text{C}$	27	-	ns
Reverse Recovery Charge	Q_{rr}		20	-	nC
Reverse Recovery Current	I_{RRM}		1.5	-	A

* Pulse width < 300 μs , duty cycle < 2%

Ratings and Characteristics Curves

Figure 1
Typical Forward Characteristics

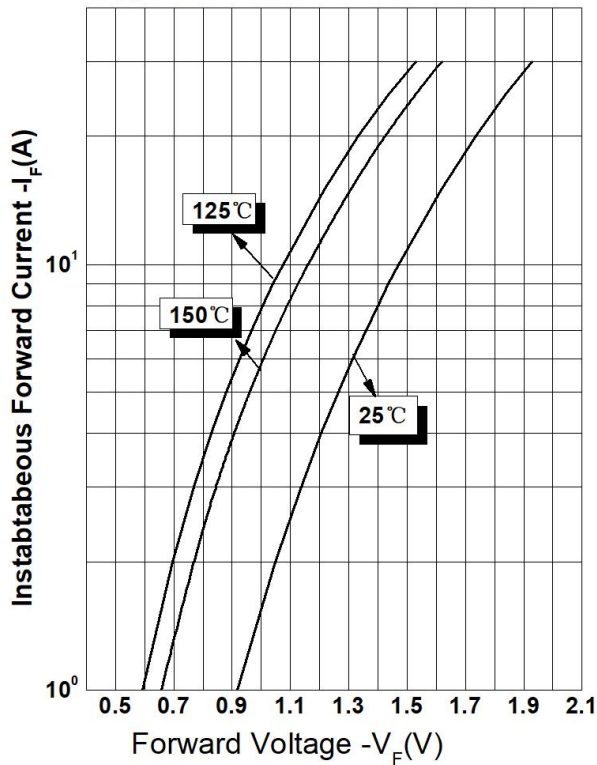


Figure 2
Typical Reverse Characteristics

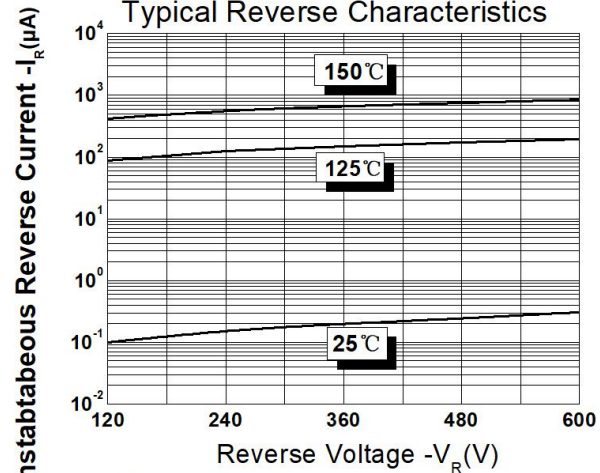
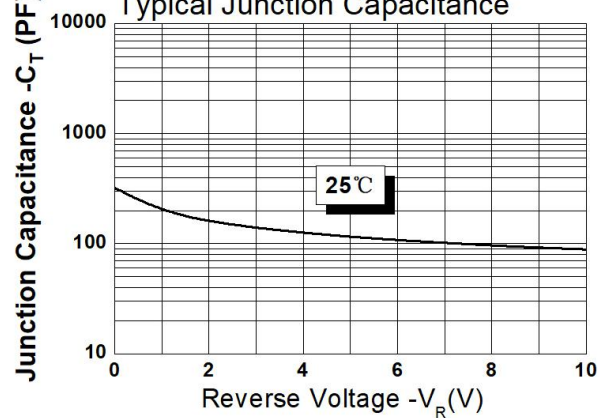


Figure 3
Typical Junction Capacitance



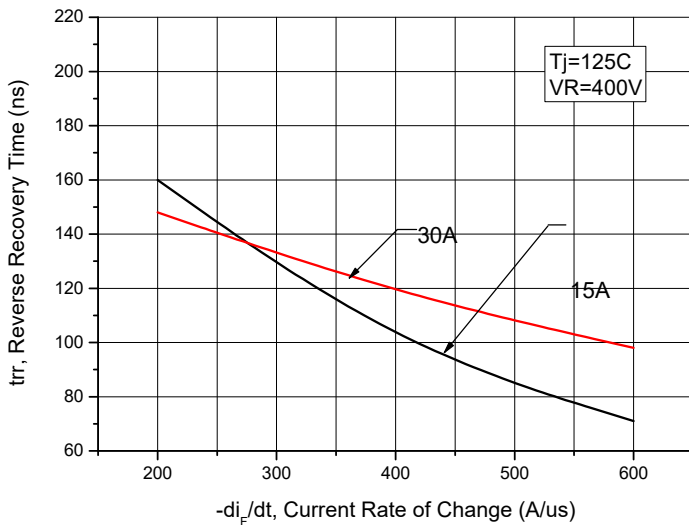


Figure 4. Reverse Recovery Time vs. Current Rate of Change

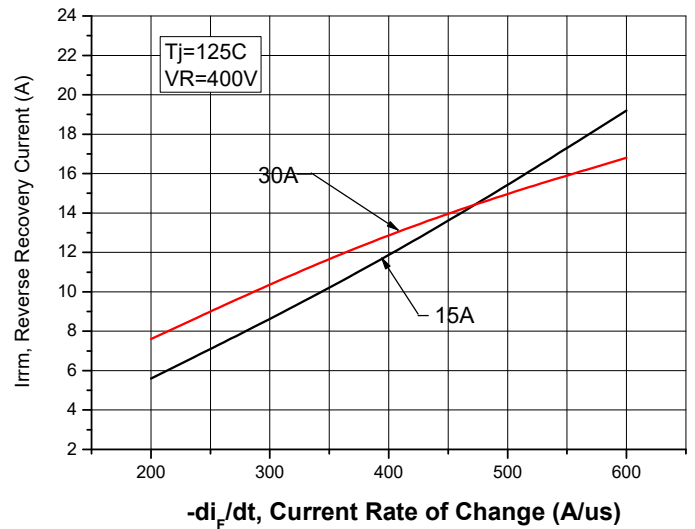


Figure 5. Reverse Recovery Current vs. Current Rate of Change

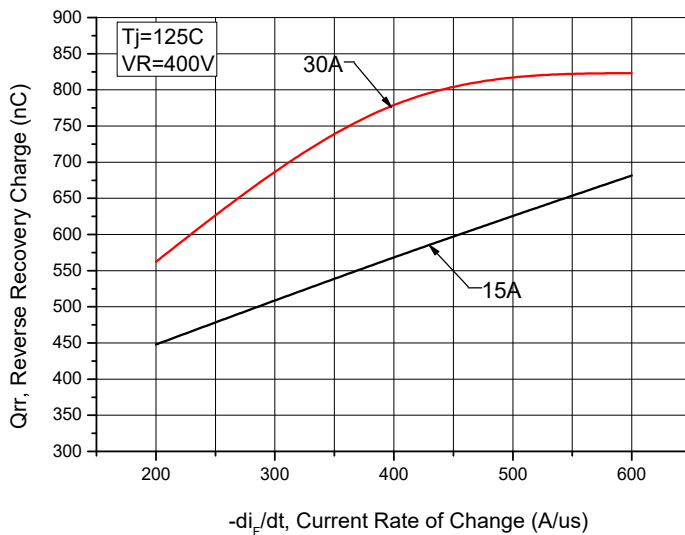


Figure 6. Reverse Recovery Charge vs. Current Rate of Change

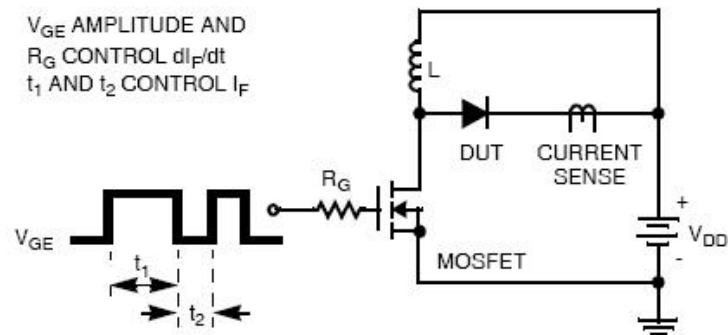
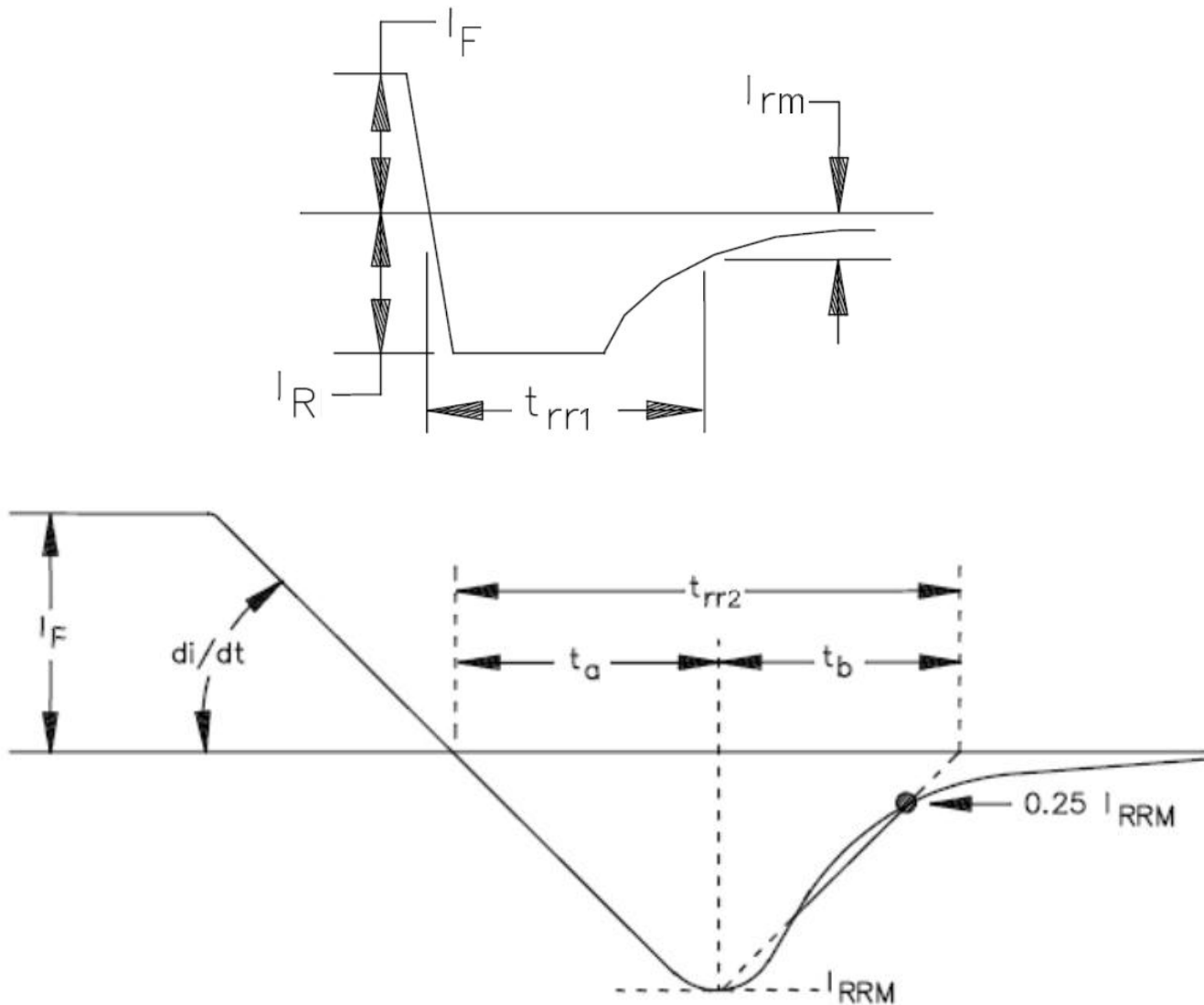


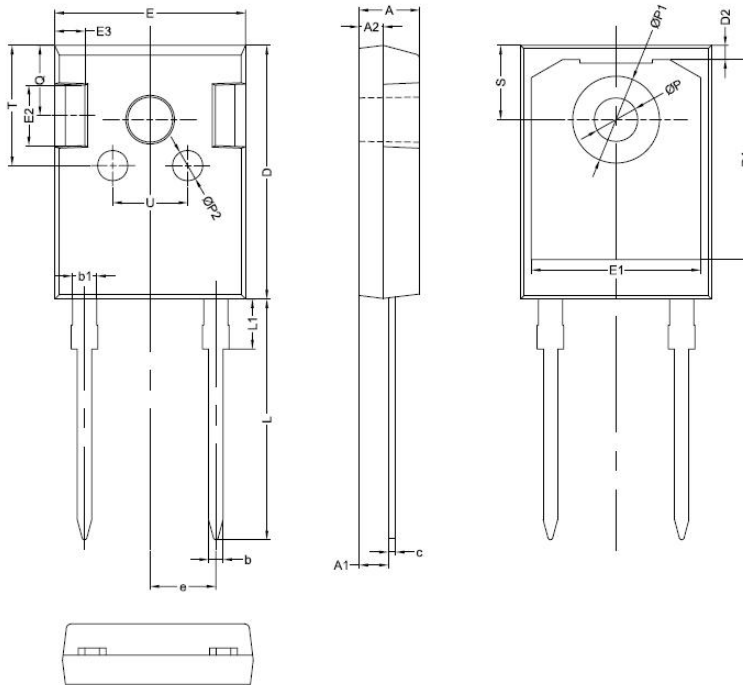
Figure 7. Diode Test Circuit



Note: 1. t_{rr1} MIL-STD-750 Test Method 4031, condition "B".
2. t_{rr2} MIL-STD-750 Test Method 4031, condition "D".

Figure 8 - Reverse Recovery Waveform

Mechanical Dimensions TO-247AC



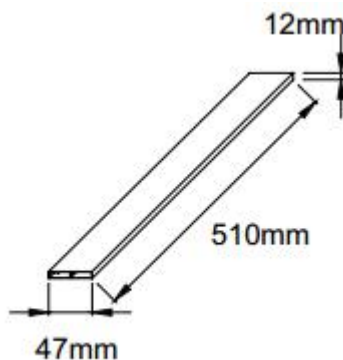
SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.80	5.00	5.20
A1	2.20	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.35
b1	1.80	2.00	2.20
c	0.50	0.60	0.75
D	20.30	21.00	21.20
D1		16.58	
D2		1.17	
E	15.60	15.80	16.00
E1		14.02	
E2		5.00	
E3		2.50	
e		5.44	
L	19.42	19.92	20.42
L1		4.13	
P	3.50	3.60	3.70
P1	7.1	7.19	7.40
P2		2.50	
Q		5.80	
S	6.05	6.15	6.25
T		10.00	
U		6.20	

Ordering Information

Device	Package	Plating	Shipping
SDUR60Q60W	TO-247AC(Pb-Free)	Pure Sn	25pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

SDUR = Device Type
60 = Forward Current (60A)
Q = Q
60 = Reverse Voltage (600V)
W = Configuration
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

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